



IXFX32N100Q3 Information



For Reference Only

Part Number IXFX32N100Q3

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1000V 32A PLUS247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXFX32N100Q3 Specifications

Manufacturer Part Number IXFX32N100Q3 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 195nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9940pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1250W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 195nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature Supplier Device Package PLUS247?-3 Package / Case	Manufacturer Part Number	IXFX32N100Q3
Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 195nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9940pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1250W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Manufacturer	IXYS
Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 195nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9940pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1250W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Category	Discrete Semiconductor Products
SeriesHiPerFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1000VCurrent - Continuous Drain (Id) @ 25°C32A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id6.5V @ 8mAGate Charge (Qg) (Max) @ Vgs195nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9940pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1250W (Tc)Rds On (Max) @ Id, Vgs320 mOhm @ 16A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 195nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9940pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1250W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case Took Care and Care	Package	TO-247-3
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Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 32A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature Supplier Device Package PLUS247?-3 Package / Case 1000V 32A (Tc) 55°C « 150°C 10V Tol 45 (Tc) 46 (A) 10V Operating Temperature -55°C ~ 150°C (TJ) Through Hole Supplier Device Package PLUS247?-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature Supplier Device Package PLUS247?-3 Package / Case 32A (Tc) 40 55°C ~ 150° Toy Through Hole Supplier Device Package PLUS247?-3 To-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 195nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9940pF @ 25V Vgs (Max) ### ### ### ### ### #### #### ########	Drain to Source Voltage (Vdss)	1000V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Pulysey (Case) Fet SmA 195nC @ 10V 19940pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Current - Continuous Drain (Id) @ 25°C	32A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 9940pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case 195nC @ 10V 195nC @ 150V 10V 10V 10V 10V 10V 10V 10V	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-247-3	Vgs(th) (Max) @ Id	6.5V @ 8mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)1250W (Tc)Rds On (Max) @ Id, Vgs320 mOhm @ 16A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	195nC @ 10V
FET Feature - Power Dissipation (Max) 1250W (Tc) Rds On (Max) @ Id, Vgs 320 mOhm @ 16A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	9940pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs320 mOhm @ 16A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Power Dissipation (Max)	1250W (Tc)
Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	320 mOhm @ 16A, 10V
Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	PLUS247?-3
Report errors?	Package / Case	TO-247-3
		Report errors?

IXFX32N100Q3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFX32N100Q3 Payment Methods





















IXFX32N100Q3 Shipping Methods













If you have any question about IXFX32N100Q3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com